



Vanderbilt Engineering



Cosmic Ray Effects on Micro-Electronics (CRÈME) Tools

Brian Sierawski
2017 SEESAW

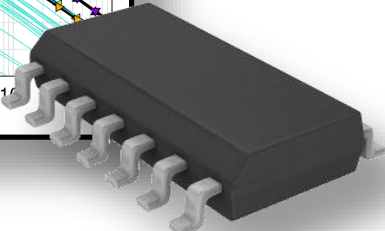
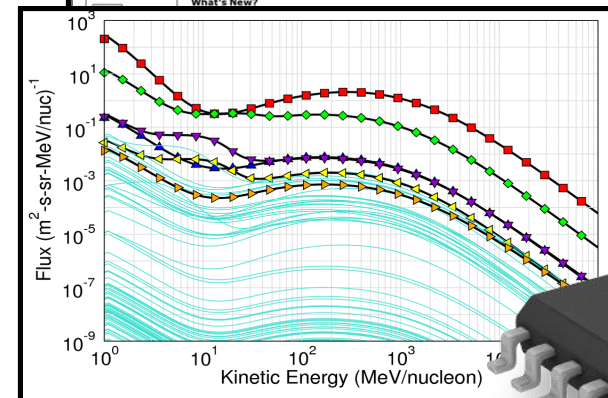
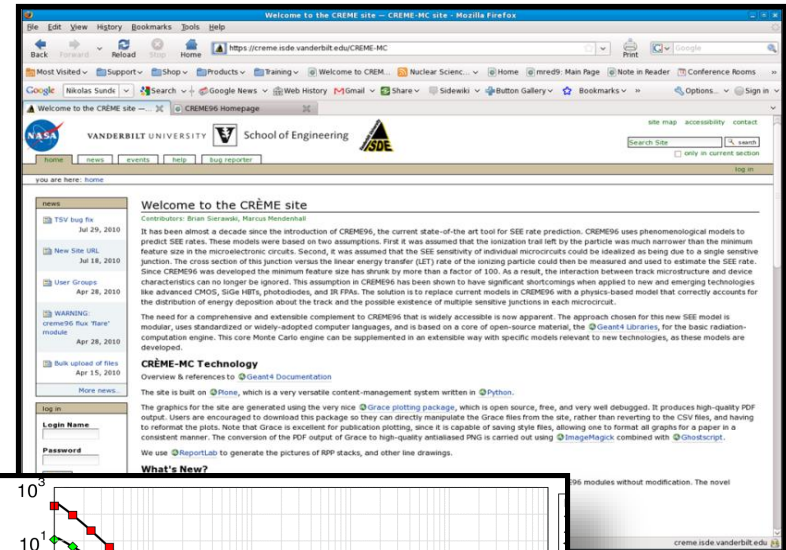


CRÈME Website



Vanderbilt Engineering

- ISDE hosts the CRÈME tool suite for predicting **on-orbit error rates** and proton **total ionizing dose** in microelectronics
- While there are multiple open-access options available, none are U.S.-based and controlled except for CRÈME
- ISDE maintains the code and operation of CRÈME, ensuring trust as well as continuing access
- Supports over 2000 users!



<https://creme.isde.vanderbilt.edu>

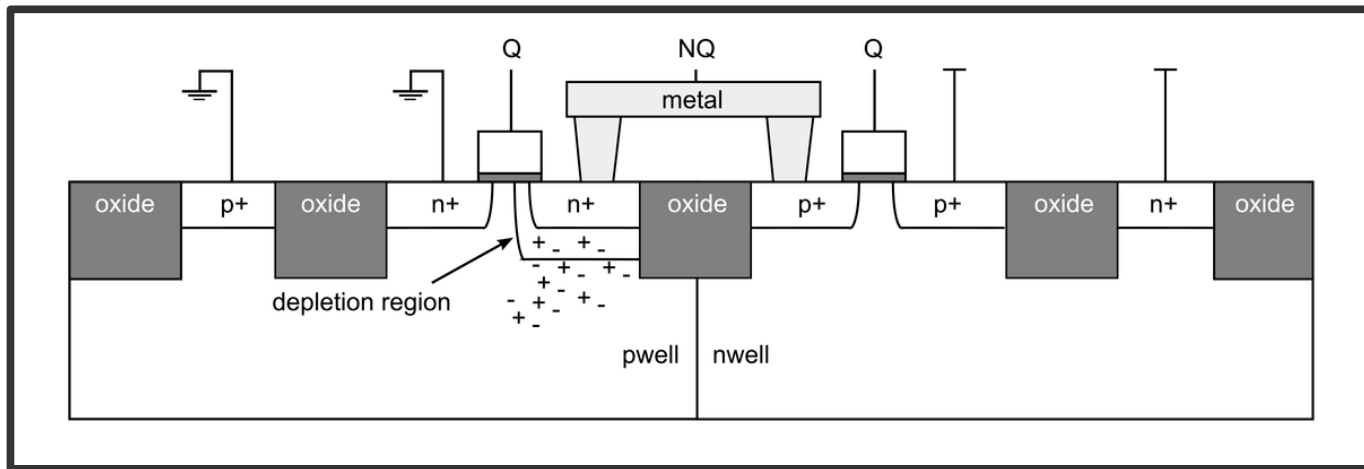


Radiation Effects on Micro-Electronics



Vanderbilt Engineering

- **Single event effects** are unwanted or erroneous responses triggered by the passage of a high energy particle through the active region of that device
 - e.g. single event upset (SEU) in memory cells
- **Total ionizing dose** due to protons and electrons causes devices to suffer threshold shifts, increased current leakage (and power consumption), timing changes, decreased functionality
- Others not addressed by CREME





CRÈME Environments



- **Near-Earth particle environment (Sawyer & Vette '76)**
 - Extracted from tables of AP8 proton fluxes
 - User selects between solar minimum and solar maximum
- **Geomagnetic shielding (Nymmik '91)**
 - Precomputed vertical cutoff magnetic rigidity values
 - Generates a geomagnetic transmission function (percent vs rigidity)
 - User selects between quiet and stormy conditions
- **Galactic cosmic ray environment (Nymmik '92)**
 - Relates intensity to Wolf sunspot number
 - Typically transported through spherical shell shielding
 - Reduced to linear energy transfer spectrum
- **Solar particle events**
 - Based on the October 1989 event, provides worst-week, worst-day and peak 5 minute fluxes

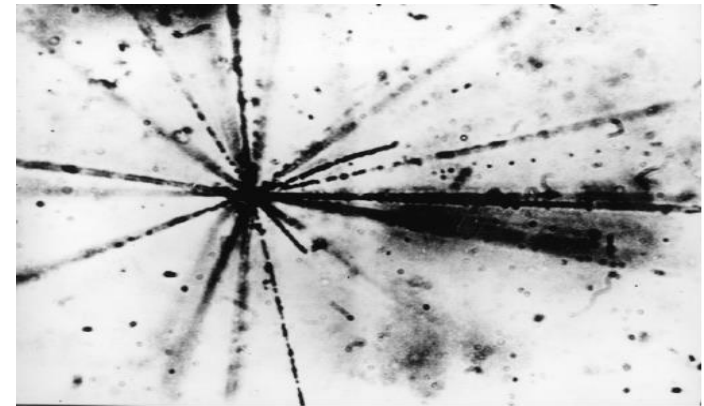
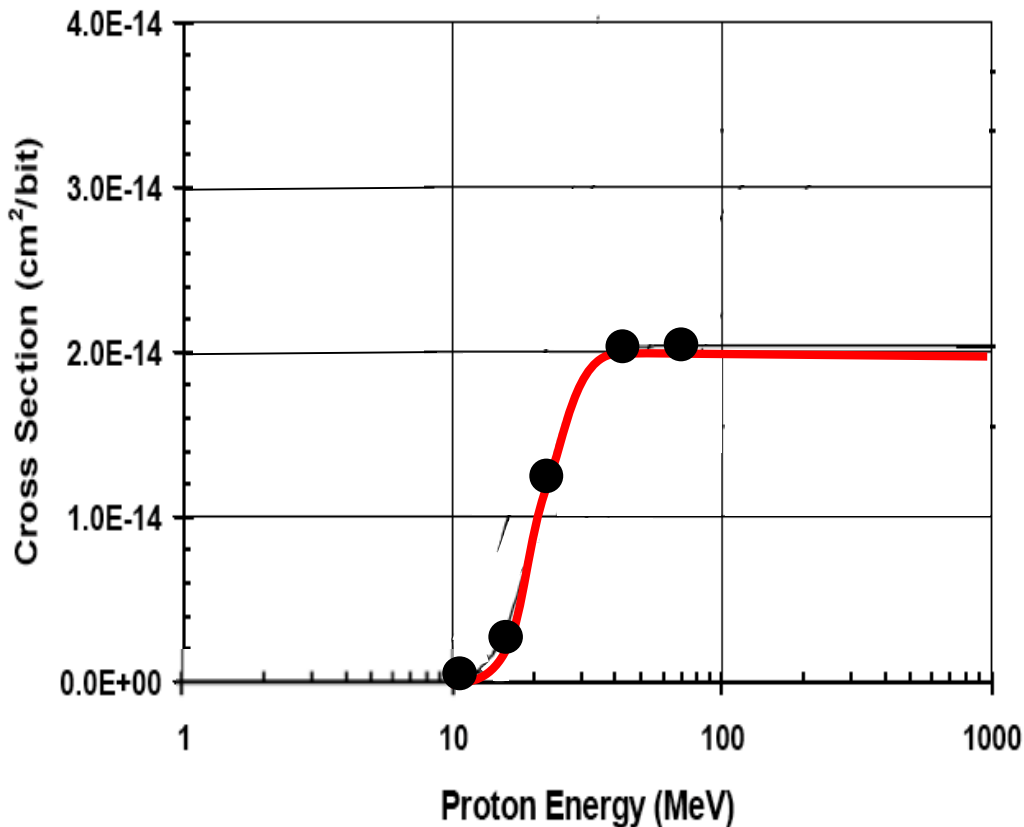


Ground Test: Proton-induced Cross Section



Vanderbilt Engineering

$$\text{Cross-section (cm}^2\text{/bit)} = \# \text{ of errors} / (\text{fluence} \cdot \# \text{bits})$$



Indirect

After Petersen, NSREC SC, 2008

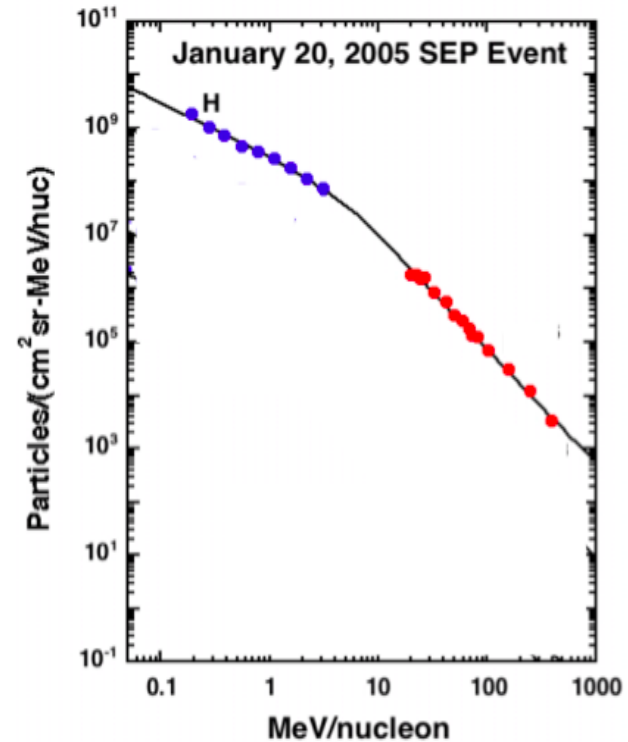
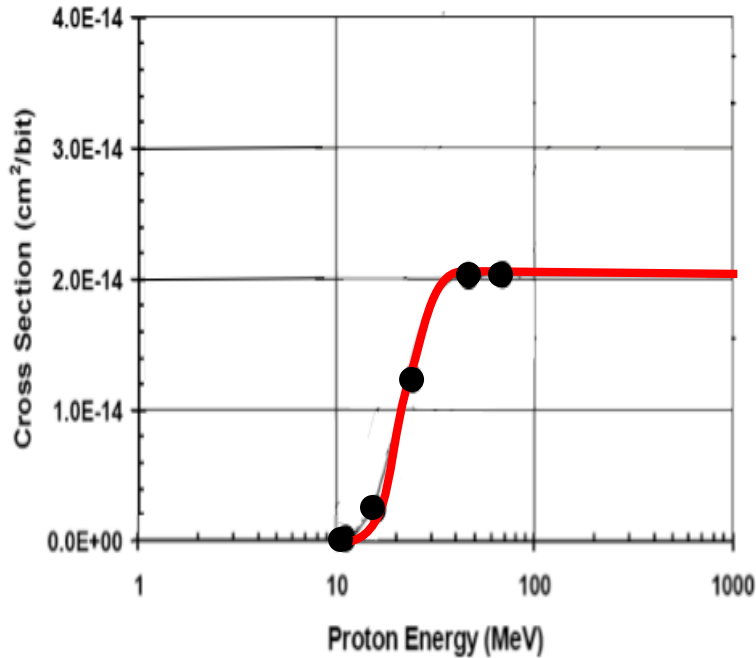


Proton Event Rate Predictions (Circa 1980)



Vanderbilt Engineering

$$\text{SEE On-Orbit Rate} = \int \text{Measured Cross Section over a certain energy} * \text{Space proton Flux at the energy } dE$$



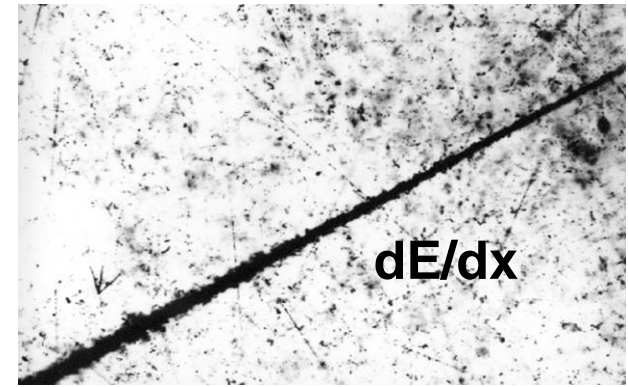
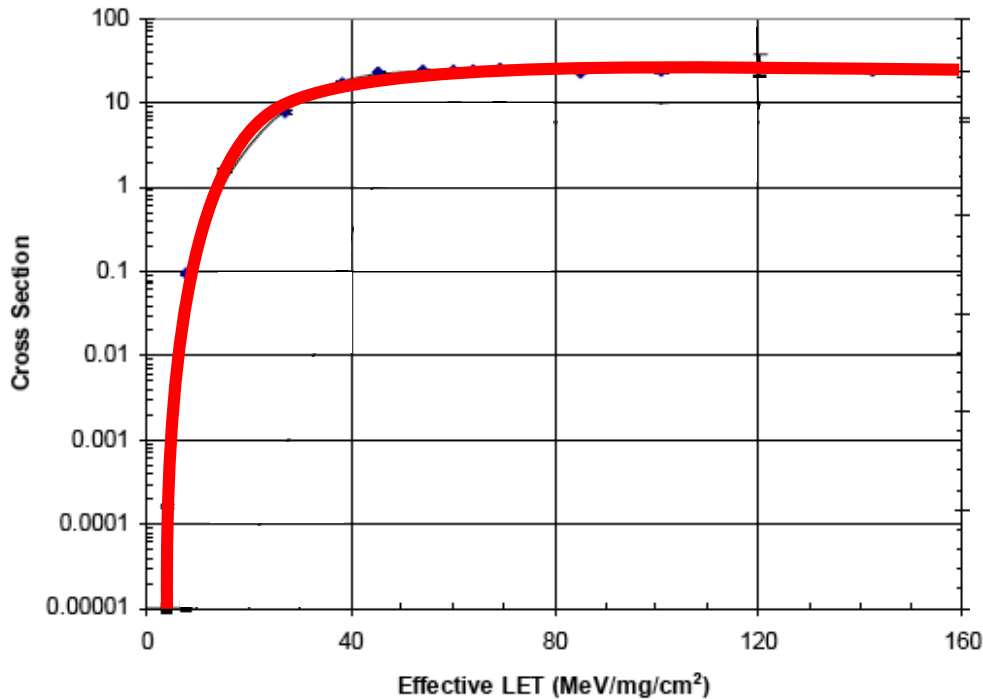


Ground Test: Heavy Ion Cross Section



Vanderbilt Engineering

Cross-section (cm^2) = # of errors / fluence



Direct

After Petersen, NSREC SC, 2008

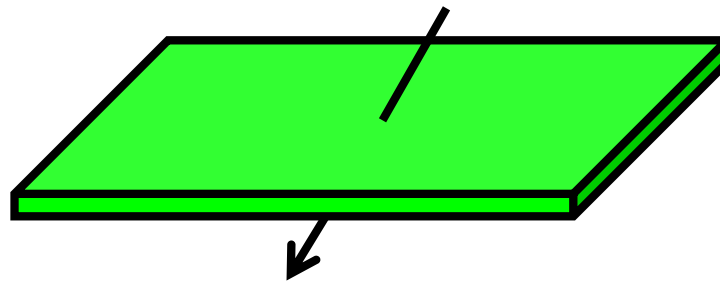


Ion Event Rate Predictions (Circa 1980)



Vanderbilt Engineering

- **Pickel and Blandford** investigated upsets in silicon NMOS dynamic RAM
- **Introduced right parallelepiped (RPP) sensitive volume**
 - Diffusion ignored
- **Sensitive region transistor diffusion, connected to storage capacitor**
- **Sensitive volume approximated as 21 μm x 3.5 μm RPP**
- **Integration over path length distribution yields rate**



$$Q_{\text{crit}} = 0.25 \text{ pC}$$

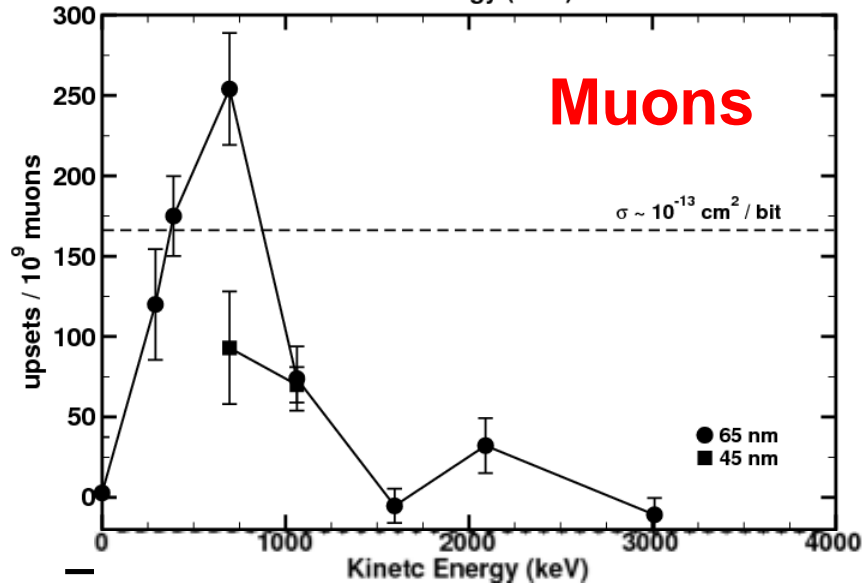
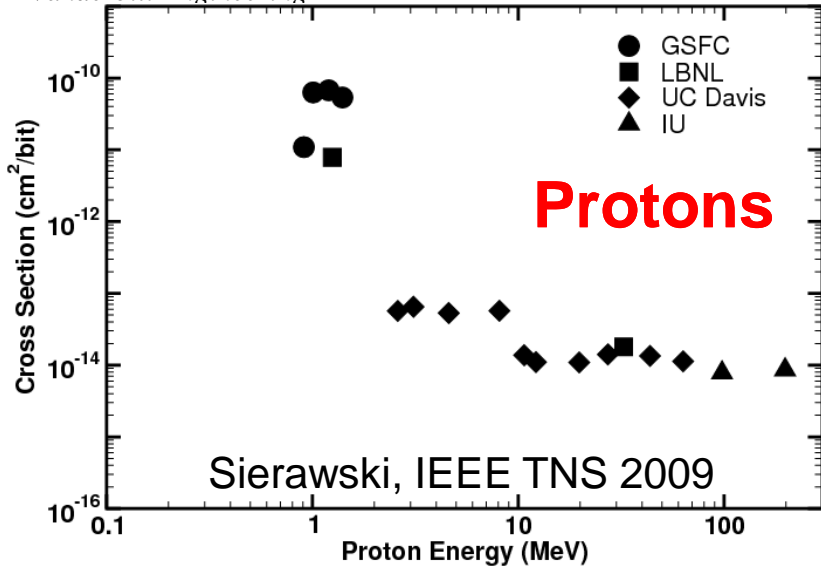
J. C. Pickel and J. T. Blandford, Jr., "Cosmic Ray Induced Errors in MOS Memory Cells," IEEE Trans. on Nucl. Sci., vol. 25, no. 6, pp. 1166-1171, 1978.



SEUs from Lightly Ionizing Particles

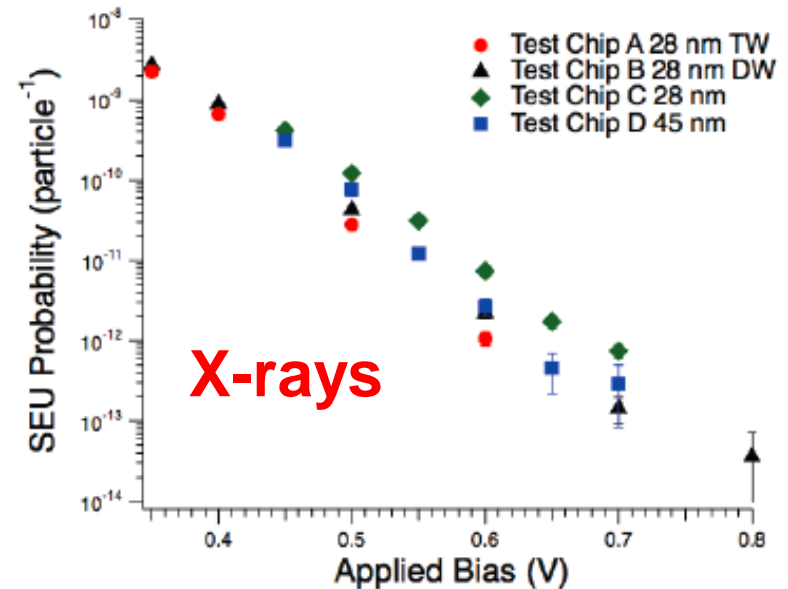


Vanderbilt Engineering



Sierawski, IEEE TNS 2010

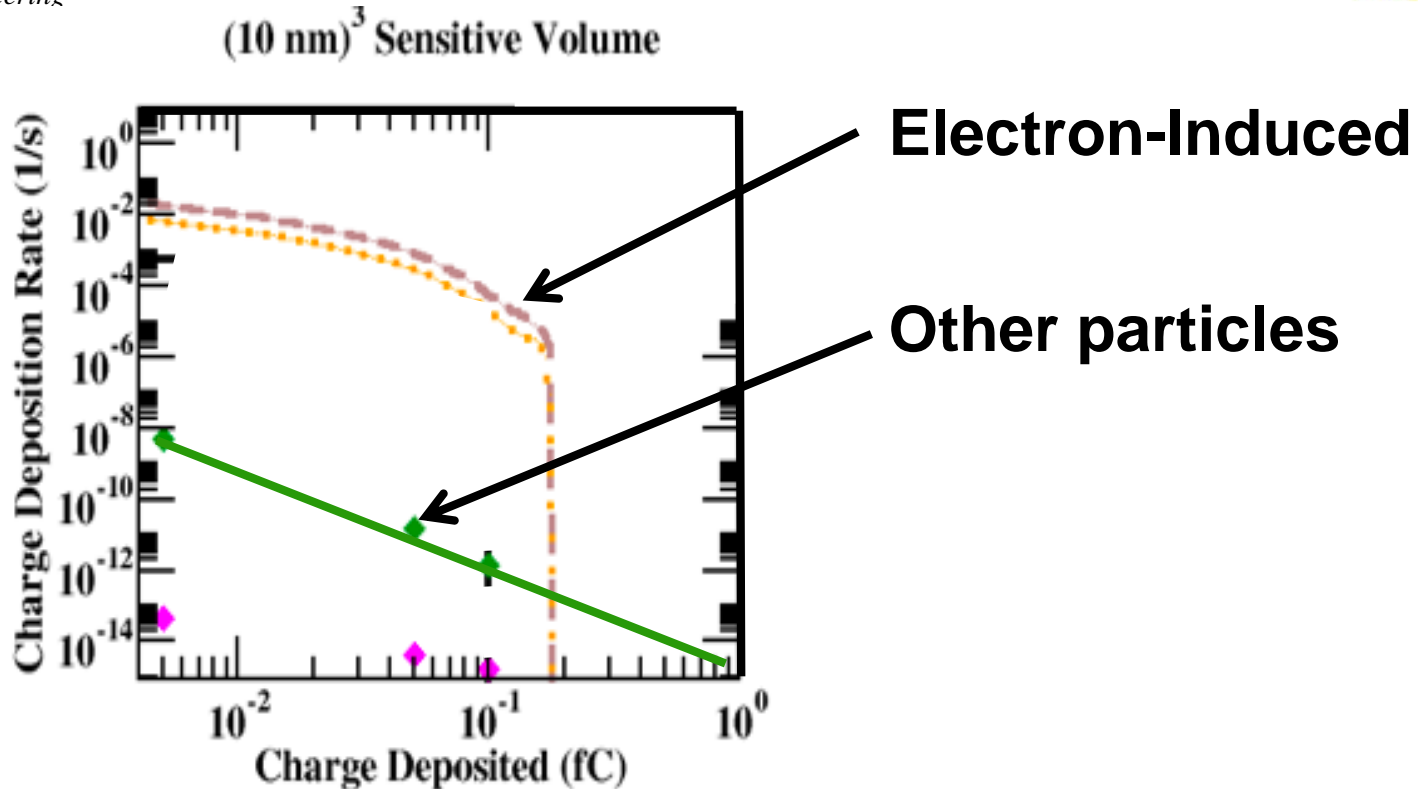
- Decreasing features sizes have lead to a reduction in critical charge
- With $Q_{\text{crit}} < 1$ fC SRAMs have become sensitive to effects from lightly ionizing particles



King, IEEE TNS 2013



Estimated SEU rates: GEO



- SEU rates are dominated by electron environment if critical charge is low enough and geometry is large enough
- This is true for other particles environments

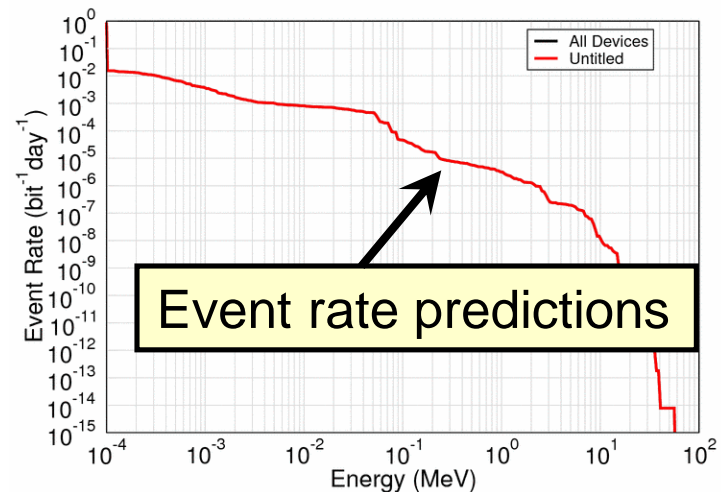
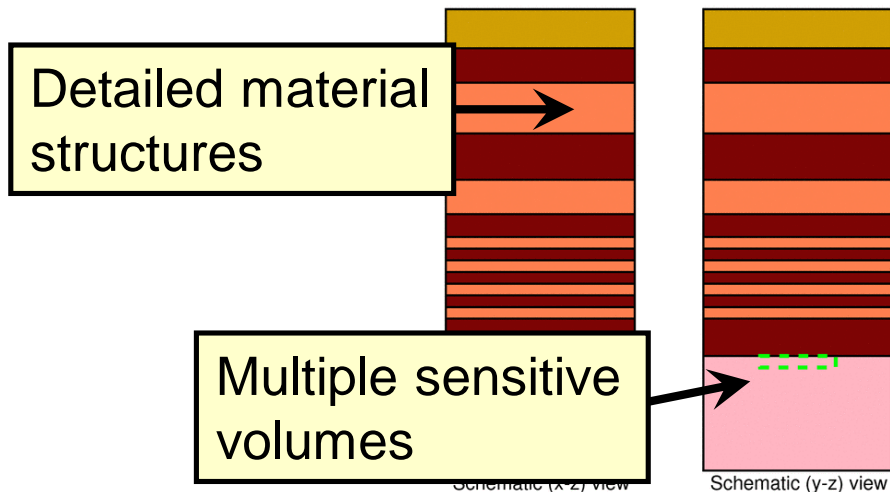
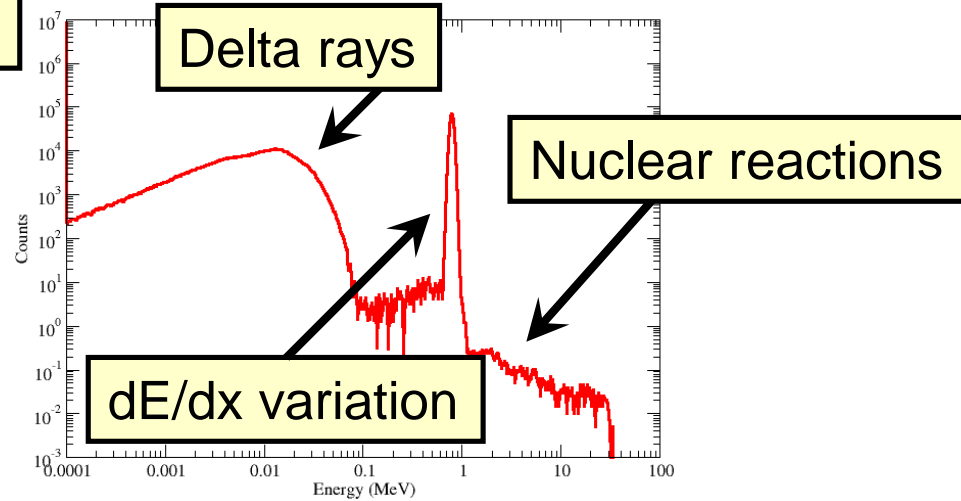
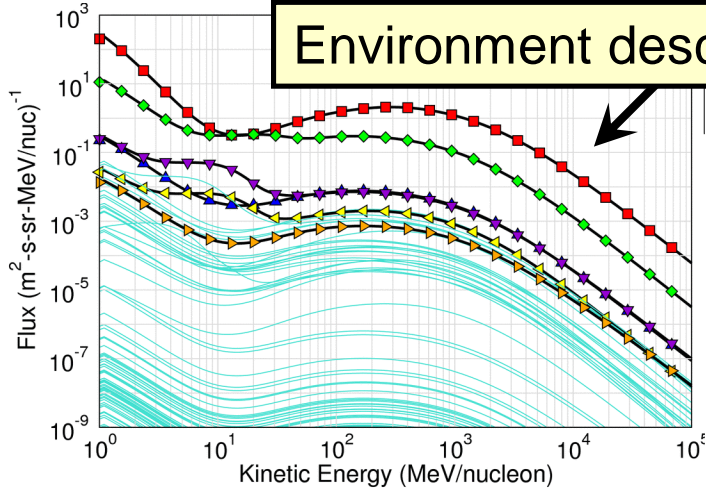
J. M. Trippe *et al.*, "Electron-Induced Single Event Upsets in 28 nm and 45 nm Bulk SRAMs," in *IEEE Trans. Nucl. Sci.*, vol. 62, no. 6, pp. 2709-2716, Dec. 2015.



Monte Carlo Rate Predictions



Vanderbilt Engineering



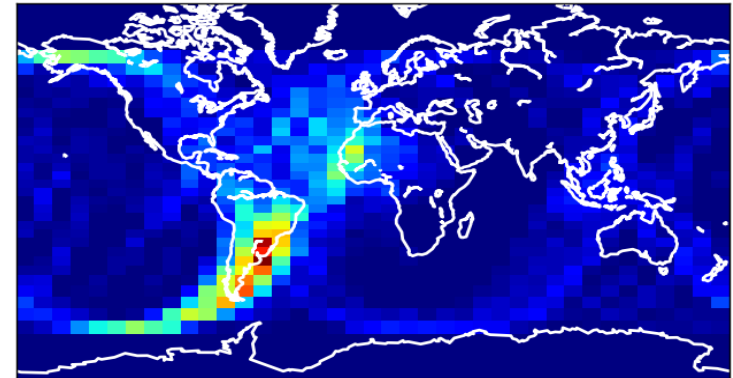
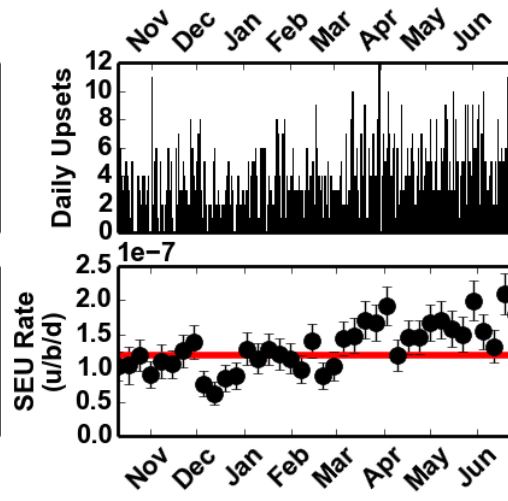
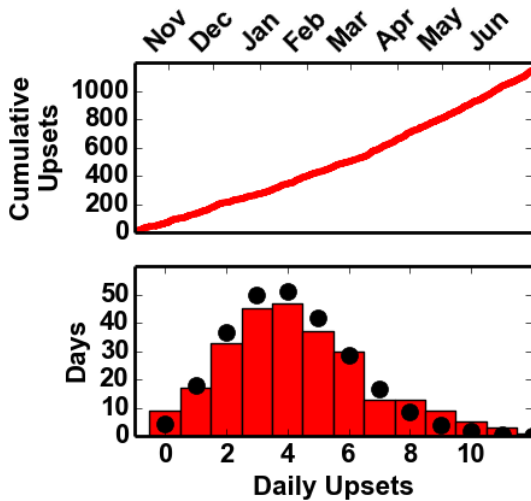
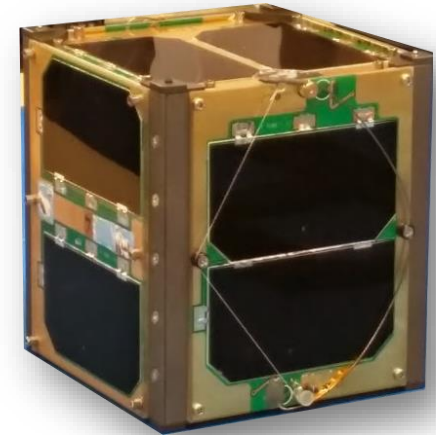


RadFx Missions



Vanderbilt Engineering

- Launched Oct. 8, 2015 on board Atlas 5 from Vandenberg, CA
- Achieved 800 – 500 km, 65° inclination orbit
- Carries Vulcan payload (1 LEP) with 8 x 4Mb SRAM (ISSI IS64WV25616B) SEU experiment
- Nearly world-wide radio coverage provided by amateur radio community
 - Reports single event upsets, resets, power





Conclusions



Vanderbilt Engineering

- **Combating evolution of environments, devices, and tool use by**
 - Incorporating AP9, updating GCR and geomagnetic models
 - Applying Monte Carlo methods to capture device response
 - Developing an API to access CREME96 calculations
 - Operating a CubeSat program to generate on-orbit datasets for advanced memories
- **Collaboration with partners is necessary for continued improvement**



References



Vanderbilt Engineering

- **R.A. Nymmik, "An Approach to Determination of Real Cosmic Ray Rigidities", Proc. 22nd Internat. Cosmic Ray Conf. (Dublin) 3, 652 (1991).**
- **R.A. Nymmik, M.I. Panasyuk, T.I. Pervaja, and A.A. Suslov, "A Model of Galactic Cosmic Ray Fluxes", Nucl. Tracks Radiat. Meas. 20, 427 (1992).**
- **D.M. Sawyer and J.I. Vette, "Trapped Particle Environment for Solar Maximum and Solar Minimum (AP8)", NSSDC Report 76-06, (1976).**

